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October 2013

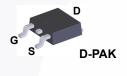
# FQD2N100 / FQU2N100 N-Channel QFET® MOSFET 1000 V, 1.6 A, 9 $\Omega$

#### **Description**

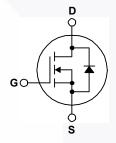
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 1.6 A, 1000 V,  $R_{DS(on)}$  = 9  $\Omega$  (Max.)@  $V_{GS}$  = 10 V,  $I_D$  = 0.8 A
- Low Gate Charge (Typ. 12 nC)
- Low Crss (Typ. 5 pF)
- 100% Avalanche Tested
- RoHS Compliant







#### **Absolute Maximum Ratings** $T_c = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		FQD2N100TM / FQU2N100TU	Unit
V <sub>DSS</sub>	Drain-Source Voltage		1000	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		1.6	Α
	- Continuous (T <sub>C</sub> = 100°C	)	1.0	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	6.4	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	160	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	1.6	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *		2.5	W
_	Power Dissipation (T <sub>C</sub> = 25°C)		50	W
	- Derate above 25°C		0.4	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FQD2N100TM FQU2N100TU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 2.5		
В	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	110	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (* 1 in² pad of 2 oz copper), Max.	50	

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQD2N100	FQD2N100TM	DPAK	330 mm	16 mm	2500
FQU2N100	FQU2N100TU	IPAK	-	-	70

Symbol	Parameter	eter Test Conditions		Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	1000			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.976		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 1000 V, V <sub>GS</sub> = 0 V			10	μΑ
		V <sub>DS</sub> = 800 V, T <sub>C</sub> = 125°C			100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.8 A		7.1	9	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 0.8 A		1.9		S
C <sub>iss</sub>	Input Capacitance Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		400	520 52	pF pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1.0 MHz		5	6.5	pF
Switch	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 500 V, I <sub>D</sub> = 2.0 A,		13	35	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$	/	30	70	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			25	60	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		35	80	ns
Qg	Total Gate Charge	V = 200 V I = 2.0 A		12	15.5	nC
		$V_{DS} = 800 \text{ V}, I_{D} = 2.0 \text{ A},$		0.5		~^
	Gate-Source Charge	V <sub>= 2</sub> = 10 V		2.5		nC
Q <sub>gs</sub>	Gate-Source Charge Gate-Drain Charge	V <sub>GS</sub> = 10 V (Note 4)		6.5		
Q <sub>gs</sub> Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)				nC
Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-S</b>		nd Maximum Ratings				
Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-S</b>	Gate-Drain Charge	nd Maximum Ratings ode Forward Current		6.5		nC
Q <sub>gs</sub> Q <sub>gd</sub> Drain-S I <sub>S</sub> I <sub>SM</sub>	Gate-Drain Charge  Source Diode Characteristics at Maximum Continuous Drain-Source Dio	nd Maximum Ratings ode Forward Current		6.5	1.5	nC A
Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-S</b>	Gate-Drain Charge  Source Diode Characteristics at Maximum Continuous Drain-Source Diode Maximum Pulsed Drain-Source Diode F	nd Maximum Ratings ode Forward Current Forward Current		6.5	1.5 6.0	nC A A

Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 120mH,  $I_{AS}$  = 1.6A,  $V_{DD}$  = 50V,  $R_G$  = 25  $\Omega$ , Starting  $T_J$  = 25°C 3.  $I_{SD} \leq$  2.0A, di/dt  $\leq$  300A/µs,  $V_{DD} \leq$  BVDsS, Starting  $T_J$  = 25°C 4. Essentially independent of operating temperature

#### **Typical Characteristics**

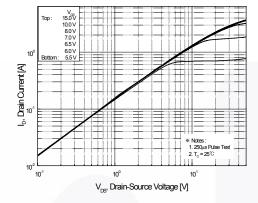


Figure 1. On-Region Characteristics

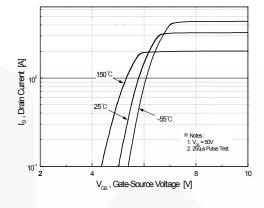


Figure 2. Transfer Characteristics

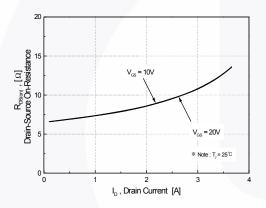


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

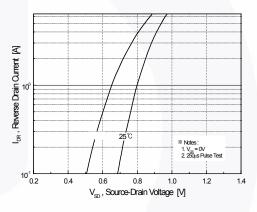


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

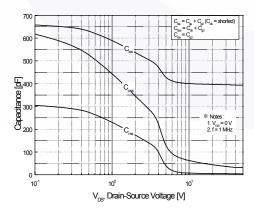


Figure 5. Capacitance Characteristics

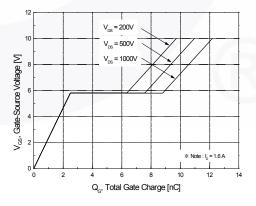
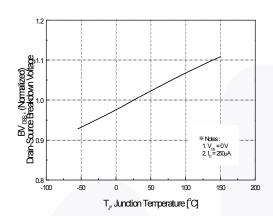


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

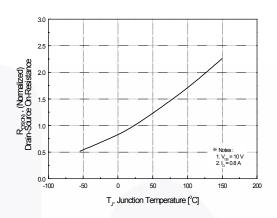


Figure 8. On-Resistance Variation vs. Temperature

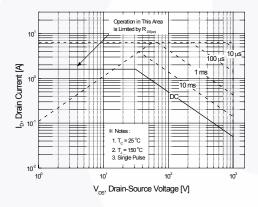


Figure 9. Maximum Safe Operating Area

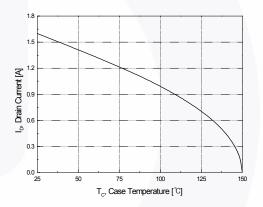


Figure 10. Maximum Drain Current vs. Case Temperature

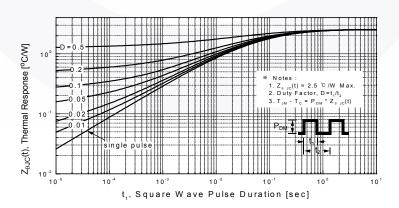


Figure 11. Transient Thermal Response Curve



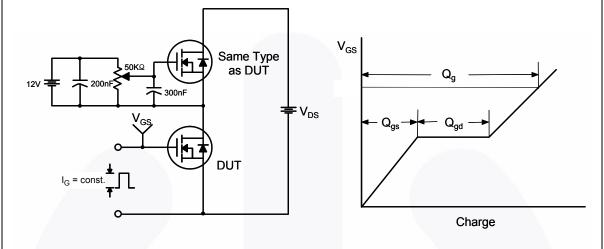


Figure 13. Resistive Switching Test Circuit & Waveforms

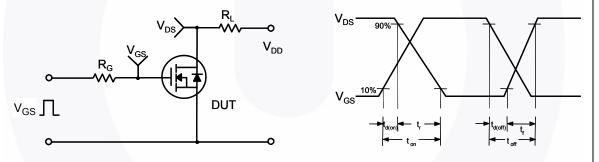
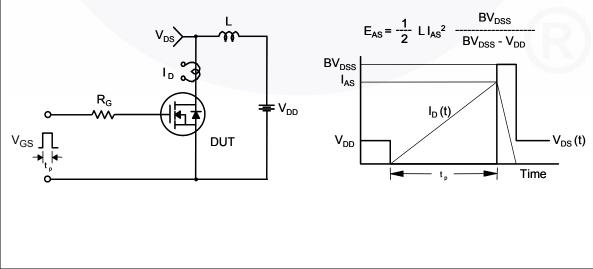
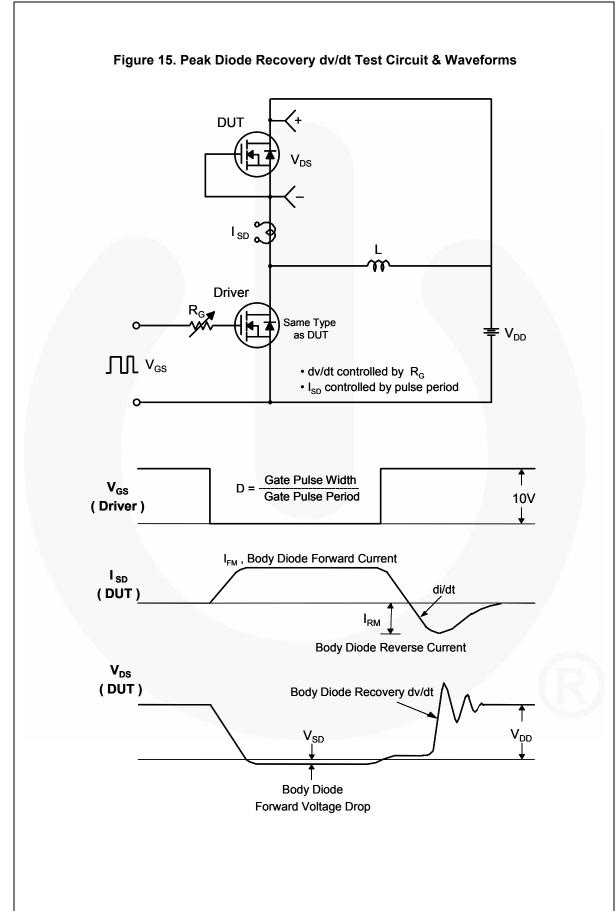


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





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#### **Mechanical Dimensions**

## TO-252 3L (DPAK)

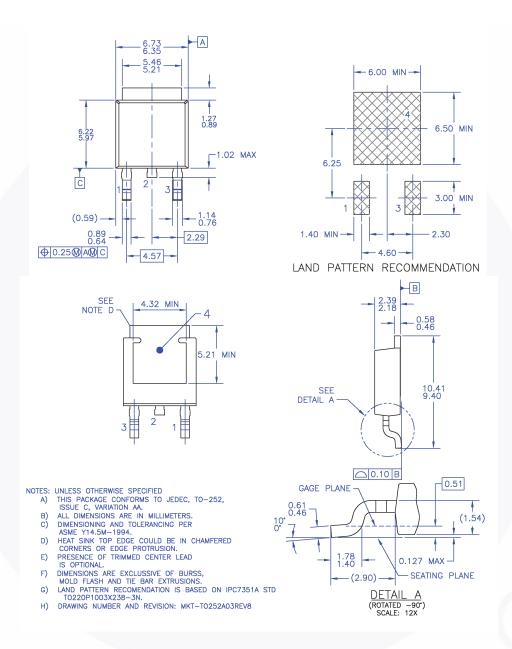


Figure 16. TO252 (D-PAK), Molded, 3 Lead, Option AA&AB

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Dimension in Millimeters

#### **Mechanical Dimensions**

## TO-251 3L (IPAK)

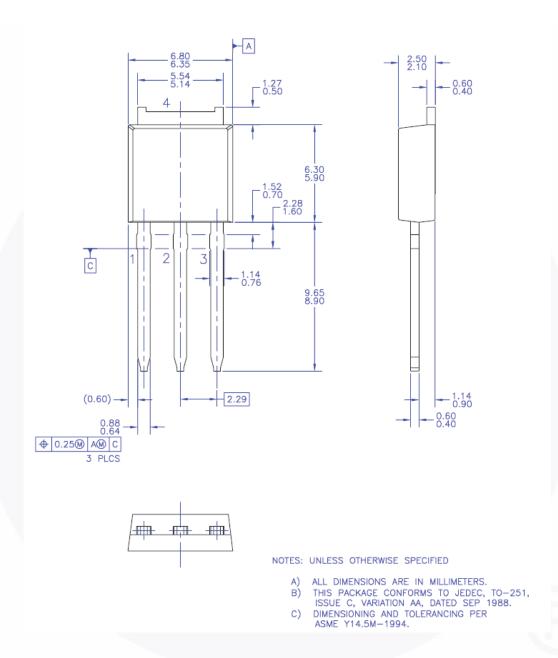


Figure 17. TO-251 (I-PAK) Molded, 3 Lead Option AA

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Dimension in Millimeters





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